Silicon NPN Power Transistors 2N6494

DESCRIPTION

·With TO-3 package
·Low collector saturation voltage
·High DC current gain
·DARLINGTON

APPLICATIONS

·General-purpose power amplifier and low frequency swithing applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

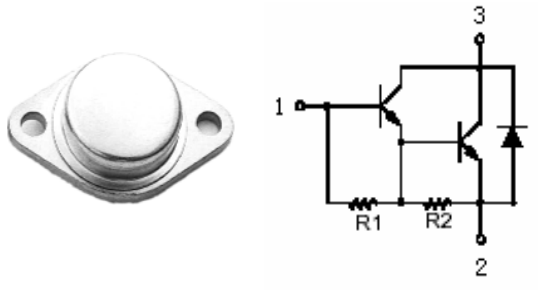

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	100	V
V_{CEO}	Collector-emitter voltage	Open base	80	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		15	A
P_D	Total Power Dissipation	T_C=25□	100	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}c}$	Thermal resistance junction to case	1.75	□/W

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CHARACTERISTICS

Tm=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=0.1 A ;I_B=0	80			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=10A ;I_B=100mA			3	V
V_{BEsat}	Base-emitter saturation voltage	I_C=10A ;I_B=100mA			4	V
V_{BE}	Base-emitter on voltage	I_C=5A ; V_{CE}=4V			2.8	V
I_{CEO}	Collector cut-off current	V_{CE}=60V; I_B=0			1.0	mA
I_{CEX}	Collector cut-off current	V_{CE}=100V; $V_{BE(off)}$=-1.5V			0.5	mA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			3.0	mA
h_{FE-1}	DC current gain	I_C=5A ; V_{CE}=4V	500			
h_{FE-2}	DC current gain	I_C=15A ; V_{CE}=4V	100			

PACKAGE OUTLINE

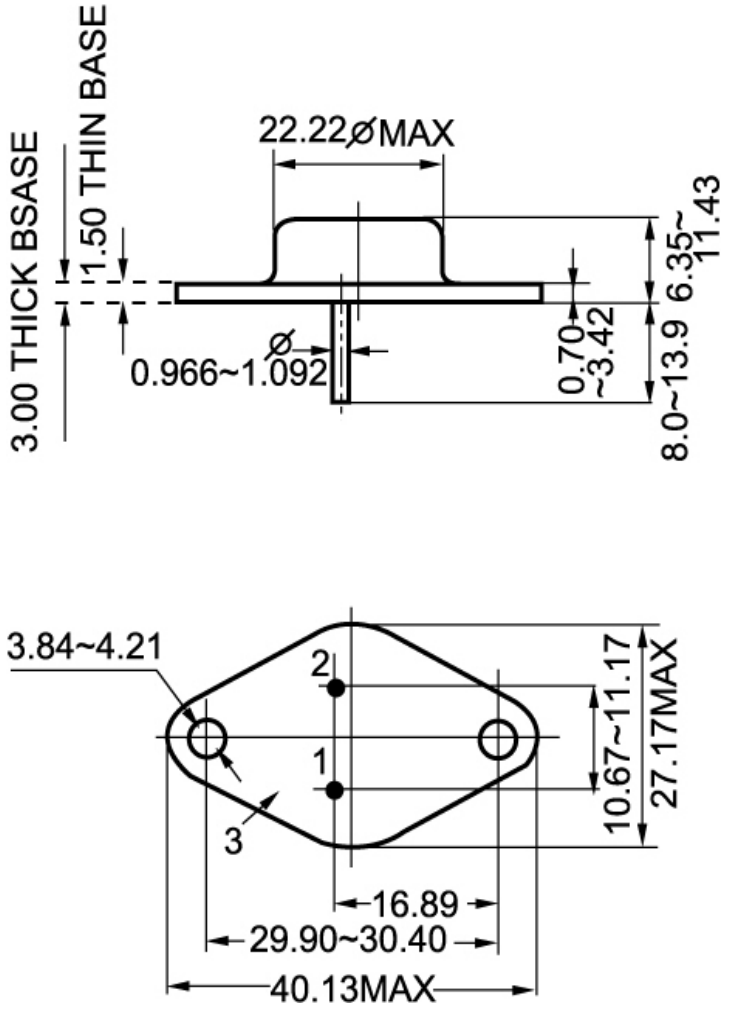

Fig.2 outline dimensions (unindicated tolerance:±0.10mm)